

B1
Cont

wherein the semiconductor element is secured in a level position and specified to operate normally only when the semiconductor element is maintained in this level position,

wherein at least part of a back of the semiconductor element is subjected to processing and a stress is applied to the semiconductor element because of the processing, wherein at least part of the semiconductor element is deformed when the semiconductor element is detached from the board, due to the stress.

B2
Sub
D1

4. (Twice Amended) The semiconductor device as defined in claim 1,

wherein the semiconductor element has a thickness of 50 μm or less in the area where the semiconductor element is processed.

B3
Sub C1

7. (Twice Amended) A method of manufacturing a semiconductor device, comprising,

securing a semiconductor element having an integrated circuit to a board so that the semiconductor element is maintained in a level position,

subjecting at least a part of a back of the semiconductor element to processing, wherein the processing applies a stress to the semiconductor element causing at least a part of the semiconductor element to deform when removed from the board, wherein the semiconductor element operates normally only when the semiconductor device is level.

8. (Twice Amended) The method of manufacturing a semiconductor device as defined in claim 7,

B³
cont.
wherein the processing step is specified to be carried out by at least one technique selected from a group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection.

9. (Twice Amended) The method of manufacturing a semiconductor device as defined in claim 7, wherein the processing step results in the semiconductor element having a thickness of 50 μm or less where the semiconductor element is processed.

34
sub 2
22. (Amended) A method of manufacturing a semiconductor device, comprising:

securing a semiconductor element having an integrated circuit to a board so as to be level with the board,

subjecting at least a part of a back of the semiconductor element to processing, wherein the processing applies a stress to the semiconductor element causing at least a part of the semiconductor element to deform when removed from the board,

wherein the subjecting at least a part of a back to processing is specified to be carried out by at least one technique selected from a group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection.